

CD4067B, CD4097B Types

CMOS Analog Multiplexers/Demultiplexers

High-Voltage Types (20-Volt Rating)

CD4067B – Single 16-Channel Multiplexer/Demultiplexer

CD4097B – Differential 8-Channel Multiplexer/Demultiplexer

The RCA-CD4067B and CD4097B CMOS analog multiplexers/demultiplexers* are digitally controlled analog switches having low ON impedance, low OFF leakage current, and internal address decoding. In addition, the ON resistance is relatively constant over the full input range.

The CD4067B is a 16-channel multiplexer with four binary control inputs, A, B, C, D, and an inhibit input, arranged so that any combination of the inputs selects one switch.

The CD4097B is a differential 8-channel multiplexer having three binary control inputs A, B, C, and an inhibit input. The inputs permit selection of one of eight pairs of switches.

A logic "1" present at the inhibit input turns all channels off.

The CD4067 and CD4097 are supplied in 24-lead dual-in-line welded-seal ceramic packages (D suffix), 24-lead dual-in-line frit-seal ceramic packages (F suffix), 24-lead dual-in-line plastic packages (E suffix), 24-lead ceramic flat packages (K suffix), and in chip form (H suffix).

*When these devices are used as demultiplexers, the channel in/out terminals are the outputs and the common out/in terminals are the inputs.

Features:

- Low ON resistance: $125\ \Omega$ (typ.) over 15 Vp-p signal-input range for $V_{DD}-V_{SS}=15\ V$
- High OFF resistance: channel leakage of $\pm 10\ pA$ (typ.) @ $V_{DD}-V_{SS}=10\ V$
- Matched switch characteristics: $R_{ON}=5\ \Omega$ (typ.) for $V_{DD}-V_{SS}=15\ V$
- Very low quiescent power dissipation under all digital-control input and supply conditions: $0.2\ \mu W$ (typ.) @ $V_{DD}-V_{SS}=10\ V$
- Binary address decoding on chip
- 5-V, 10-V, and 15-V parametric ratings
- 100% tested for quiescent current at 20 V
- Standardized symmetrical output characteristics
- Maximum input current of $1\ \mu A$ at 18 V over full package temperature range; $100\ nA$ at 18 V and $25^\circ C$
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Analog and digital multiplexing and demultiplexing
- A/D and D/A conversion
- Signal gating

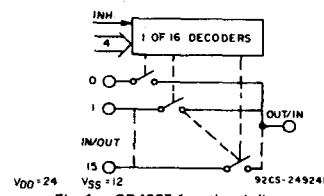
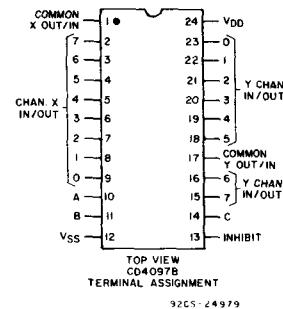
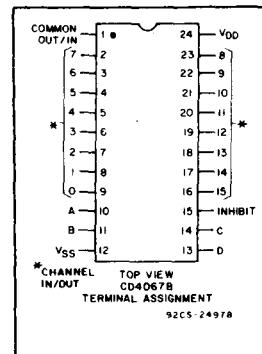


Fig. 1 – CD4067 functional diagram.

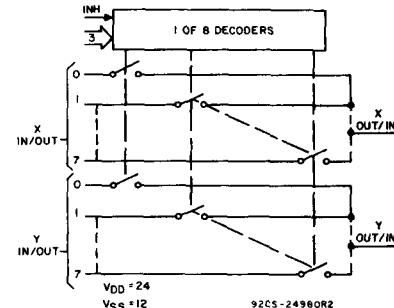


Fig. 2 – CD4097 functional diagram.

CD4067 TRUTH TABLE

A	B	C	D	Inh	Selected Channel
X	X	X	X	1	None
0	0	0	0	0	0
1	0	0	D	0	1
0	1	0	D	0	2
1	1	0	D	0	3
0	0	1	0	0	4
1	0	1	0	0	5
0	1	1	0	0	6
1	1	1	0	0	7
0	0	0	1	0	8
1	0	0	1	0	9
0	1	0	1	0	10
1	1	0	1	0	11
0	0	1	1	0	12
1	0	1	1	0	13
0	1	1	1	0	14
1	1	1	1	0	15

CD4097 TRUTH TABLE

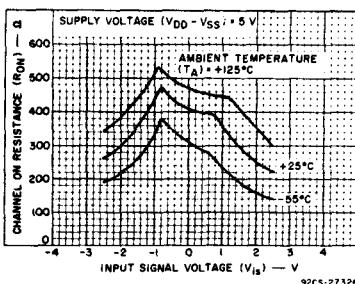
A	B	C	Inh	Selected Channel
X	X	X	1	None
0	0	0	0	0X, 0Y
1	0	0	0	1X, 1Y
0	1	0	0	2X, 2Y
1	1	0	0	3X, 3Y
0	0	1	0	4X, 4Y
1	0	1	0	5X, 5Y
0	1	1	0	6X, 6Y
1	1	1	0	7X, 7Y

CD4067B, CD4097B Types

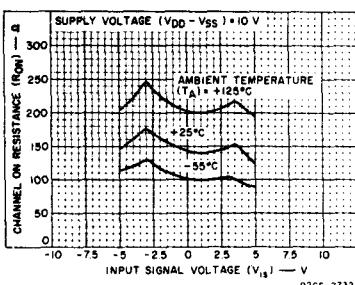
ELECTRICAL CHARACTERISTICS

CHARAC- TERISTIC	CONDITIONS			LIMITS at Indicated Temperature (°C)						Units		
				Values at -55, +25, +125 Apply to D, F, K, H pkg Values at -40, +25, +85, apply to E pkg								
	V_{IS} (V)	V_{SS} (V)	V_{DD} (V)	-55	-40	+85	+125	+25	Min.			
SIGNAL INPUTS (V_{IS}) AND OUTPUTS (V_{OS})												
Quiescent Device Cur- rent, I_{DD} Max.				5	5	5	150	150	—	0.04	μA	
				10	10	10	300	300	—	0.04	10	
				15	20	20	600	600	—	0.04	20	
				20	100	100	3000	3000	—	0.08	100	
ON-state Re- sistance $V_{SS} \leq V_{IS} \leq V_{DD}$ r_{on} Max.				0	5	800	850	1200	1300	—	470	Ω
				0	10	310	330	520	550	—	180	400
				0	15	200	210	300	320	—	125	240
Change in on-state Resistance (Between Any Two Channels) Δr_{on}				0	5	—	—	—	—	15	—	
				0	10	—	—	—	—	10	—	
				0	15	—	—	—	—	5	—	
OFF Chan- nel Leak- age Cur- rent: Any Channel OFF Max. or All Chan- nels OFF (Common OUT/IN) Max.				0	18	±100*	±1000*	—	±0.1	±100*	nA	
						—	—	—	—	5	—	
						—	—	—	—	55	—	
Capacitance: Input, C_{IS} Output, C_{OS} CD4067 CD4097 Feed- through, C_{IOS}						—	—	—	—	35	pF	
						—	—	—	—	0.2	—	
						—	—	—	—	—	—	
Propaga- tion Delay Time (Sig- nal Input to Output)	V_{DD}  $R_L = 200 \text{ k}\Omega$ $C_L = 50 \text{ pF}$ $t_r, t_f = 20 \text{ ns}$	5	—	—	—	—	—	30	60	ns		
		10	—	—	—	—	—	15	30			
		15	—	—	—	—	—	10	20			
CONTROL (ADDRESS or INHIBIT) V_C												
Input Low Voltage, V_{IL} Max.	V_{DD} thru $V_C = V_{SS}$ $I_{IS} < 2 \mu\text{A}$ on all OFF Channels	$R_L = 1 \text{ k}\Omega$	5	1.5	—	—	1.5	V				
			10	3	—	—	3					
			15	4	—	—	4					
Input High Voltage, V_{IH} Min.			5	3.5	3.5	—	—					
			10	7	7	—	—					
			15	11	11	—	—					

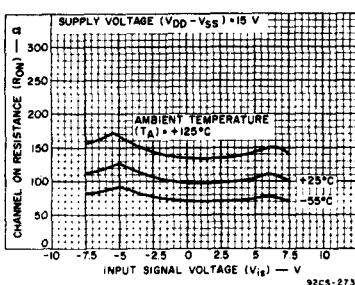
* Determined by minimum feasible leakage measurement for automatic testing.



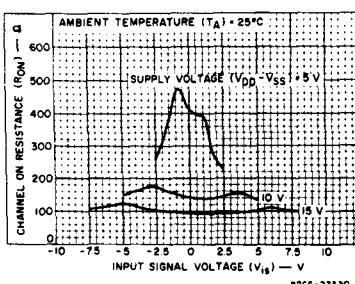
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CD4067B, CD4097B Types

ELECTRICAL CHARACTERISTICS (Cont'd)

CHARAC- TERISTIC	CONDITIONS			LIMITS at Indicated Temperature ($^{\circ}\text{C}$)						Units	
	V_{IS} (V)	V_{SS} (V)	V_{DD} (V)	Values at -55, +25, +125 Apply to D, F, K, H pkg.				+25			
				-55	-40	+85	+125	Min.	Typ.	Max.	
Input Current, I_{IN} Max.	$V_{\text{IN}} = 0, 18 \text{ V}$	18	± 0.1	± 0.1	± 1	± 1	-	$\pm 10^{-5}$	± 0.1	μA	
Propagation Delay Time: Address or Inhibit-to-Signal OUT (Channel turning ON)	$R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF}, t_{\text{f}}, t_{\text{r}} = 20 \text{ ns}$	0	5	-	-	-	-	325	650	ns	
		0	10	-	-	-	-	135	270	ns	
		0	15	-	-	-	-	95	190	ns	
Address or Inhibit-to-Signal OUT (Channel turning OFF)	$R_L = 300 \Omega, C_L = 50 \text{ pF}, t_{\text{f}}, t_{\text{r}} = 20 \text{ ns}$	0	5	-	-	-	-	220	440	ns	
		0	10	-	-	-	-	90	180	ns	
		0	15	-	-	-	-	65	130	ns	
Input Capacitance, C_{IN}	Any Address or Inhibit Input		-	-	-	-	-	5	7.5	pF	

TEST CIRCUITS

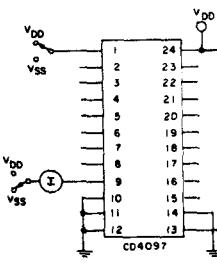
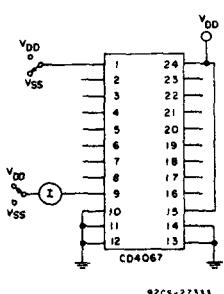


Fig. 7—OFF channel leakage current—any channel OFF.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

(Voltages referenced to V_{SS} Terminal) -0.5 to +20 V

INPUT VOLTAGE RANGE, ALL INPUTS

. -0.5 to $V_{\text{DD}} + 0.5 \text{ V}$

DC INPUT CURRENT, ANY ONE INPUT

. $\pm 10 \text{ mA}$

POWER DISSIPATION PER PACKAGE (PD):

For $T_A = -40$ to $+60^{\circ}\text{C}$ (PACKAGE TYPE E) 500 mW

For $T_A = +60$ to $+85^{\circ}\text{C}$ (PACKAGE TYPE E) Derate Linearly at $12 \text{ mW}/^{\circ}\text{C}$ to 200 mW

For $T_A = -55$ to $+100^{\circ}\text{C}$ (PACKAGE TYPES D, F, K) 500 mW

For $T_A = +100$ to $+125^{\circ}\text{C}$ (PACKAGE TYPES D, F, K) Derate Linearly at $12 \text{ mW}/^{\circ}\text{C}$ to 200 mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100 mW

OPERATING-TEMPERATURE RANGE (T_A):

PACKAGE TYPES D, F, K, H -55 to $+125^{\circ}\text{C}$

PACKAGE TYPE E -40 to $+85^{\circ}\text{C}$

STORAGE TEMPERATURE RANGE (T_{STG}) -65 to $+150^{\circ}\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch ($1.59 \pm 0.79 \text{ mm}$) from case for 10 s max. +265°C

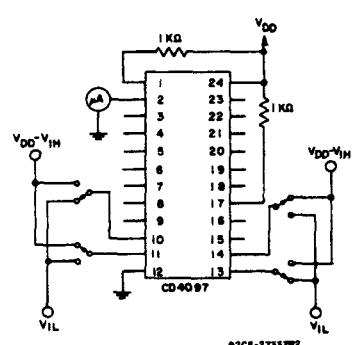
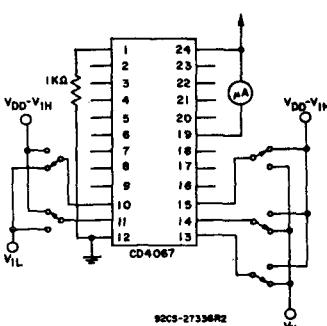


Fig. 8—Input voltage—measure <2 μA on all OFF channels
(e.g., channel 12).

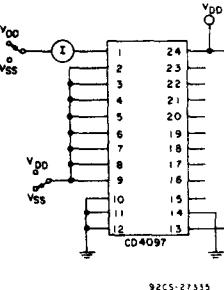
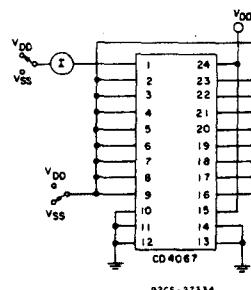


Fig. 9—OFF channel leakage current—all channels OFF.

CD4067B, CD4097B Types

ELECTRICAL CHARACTERISTICS (Cont'd)

CHARAC- TERISTIC	TEST CONDITIONS			TYPICAL VALUES	UNITS
	V _{IS} (V)	V _{DD} (V)	R _L (kΩ)		
Cutoff (-3-dB) Frequency Channel ON (Sine Wave Input)	5*	10	1	V _{OS} at Common OUT/IN $20 \log \frac{V_{OS}}{V_{IS}} = -3 \text{ dB}$	MHz
				CD4067 CD4097	
				14 20 60	
Total Harmonic Distortion, THD	2*	5	10 $f_{IS} = 1 \text{ kHz}$ sine wave	0.3 0.2 0.12	%
	3*	10			
	5*	15			
-40-dB Feedthrough Frequency (All Channels OFF)	5*	10	1	V _{OS} at Common OUT/IN $20 \log \frac{V_{OS}}{V_{IS}} = -40 \text{ dB}$	MHz
				CD4067 CD4097	
				20 12 8	
Signal Cross- talk (Fre- quency at -40 dB)	5*	10	1	Between Any 2 Channels Measured on Common CD4097 Only	MHz
				1 10 18	
				Measured on Any Channel	
Address-or- Inhibit-to- Signal Crosstalk	-	10	10*	V _{SS} =0, t _r , t _f =20 ns, V _C =V _{DD} -V _{SS} (Square Wave)	mV (Peak)

* Peak-to-peak voltage symmetrical about $\frac{V_{DD}-V_{SS}}{2}$

▲ Worst case.

* Both ends of channel.

TEST CIRCUITS (Cont'd)

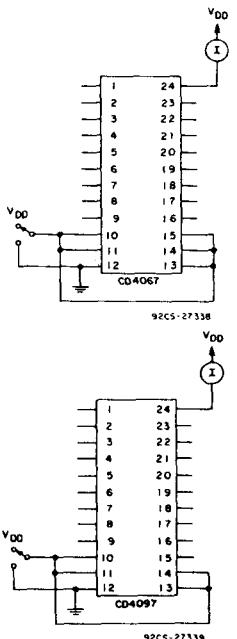


Fig. 10—Quiescent device current.

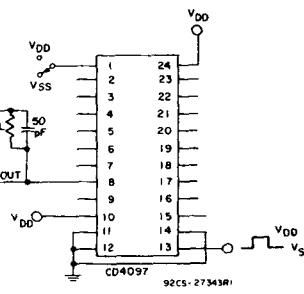
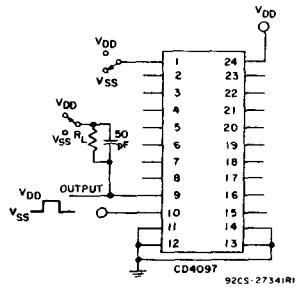
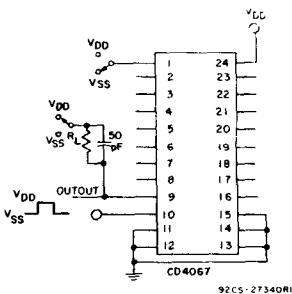
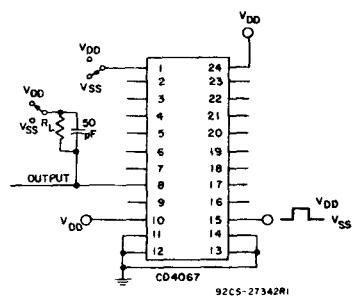


Fig. 11—Turn-on and turn-off propagation delay—address select input to signal output (e.g. measured on channel 0).

Fig. 12—Turn-on and turn-off propagation delay—
inhibit input to signal output (e.g. measured
on channel 1).

CD4067B, CD4097B Types

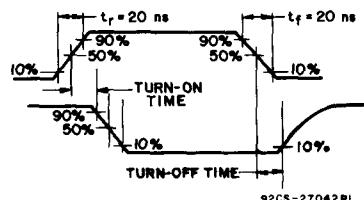
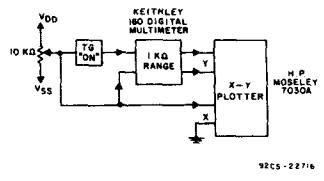


Fig. 13—Channel ON resistance measurement circuit.

Fig. 14—Propagation delay waveform channel being turned ON ($R_L = 10 \text{ k}\Omega$, $C_L = 50 \text{ pF}$).

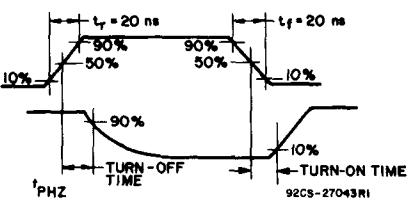


Fig. 15—Propagation delay waveform, channel being turned OFF ($R_L = 300 \text{ }\mu\text{A}$, $C_L = 50 \text{ pF}$).

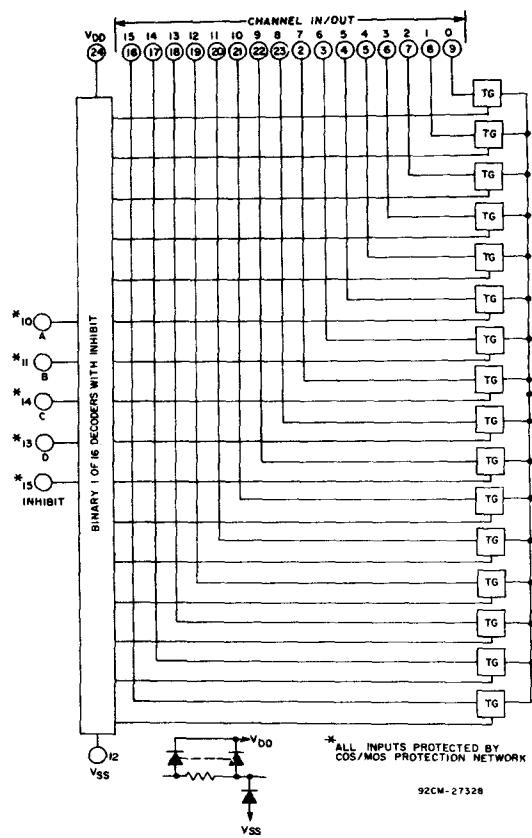


Fig. 16—CD4067 logic diagram.

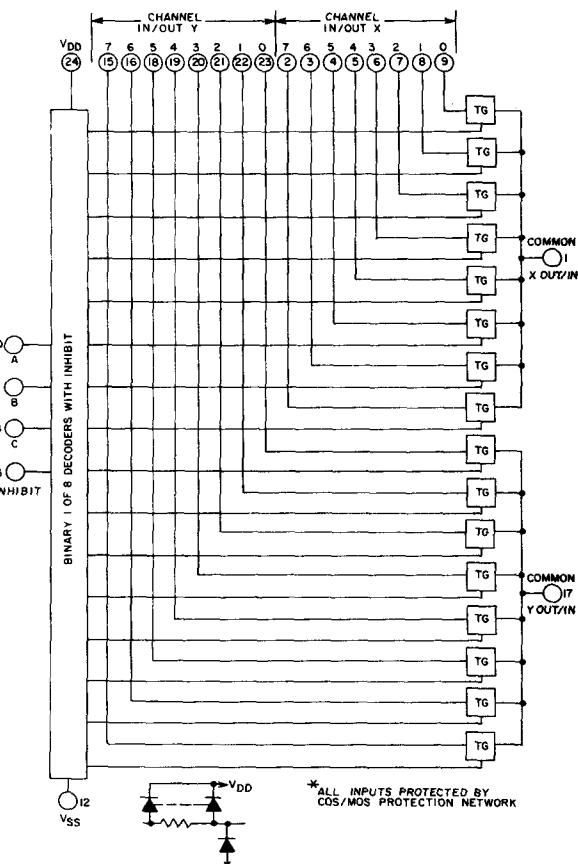


Fig. 17—CD4097 logic diagram.

CD4067B, CD4097B Types

SPECIAL CONSIDERATIONS

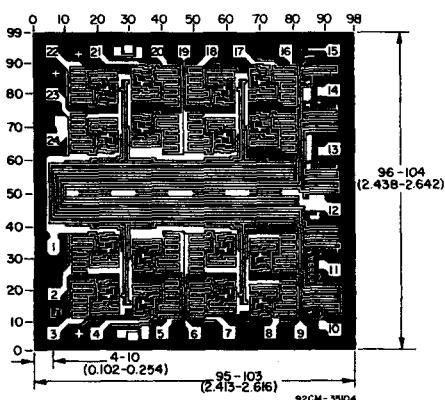
In applications where separate power sources are used to drive V_{DD} and the signal inputs, the V_{DD} current capability should exceed V_{DD}/R_L (R_L =effective external load). This provision avoids permanent current flow or clamp action on the V_{DD} supply when power is applied or removed from the CD4067B or CD4097B.

When switching from one address to another, some of the ON periods of the channels of the multiplexers will overlap momentarily, which may be objectionable in certain applications. Also when a channel is turned on or off by an address input, there is a momentary conductive path from the channel to V_{SS} , which will dump some charge from any capacitor connected to the input or output of the channel. The inhibit input turning on a channel will similarly dump some charge to V_{SS} .

The amount of charge dumped is mostly a function of the signal level above V_{SS} . Typically, at $V_{DD}-V_{SS}=10$ V, a 100-pF

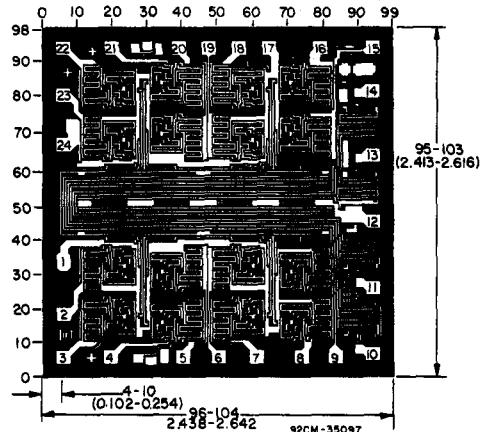
capacitor connected to the input or output of the channel will lose 3-4% of its voltage at the moment the channel turns on or off. This loss of voltage is essentially independent of the address or inhibit signal transition time, if the transition time is less than 1.2 μ s. When the inhibit signal turns a channel off, there is no charge dumping to V_{SS} . Rather, there is a slight rise in the channel voltage level (65 mV typ.) due to capacitive coupling from inhibit input to channel input or output. Address inputs also couple some voltage steps onto the channel signal levels.

In certain applications, the external load-resistor current may include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from R_{ON} values shown in ELECTRICAL CHARACTERISTICS CHART). No V_{DD} current will flow through R_L if the switch current flows into terminal 1 on the CD4067B, terminals 1 and 17 on the CD4097B.



Dimensions and pad layout for CD4067BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).



Dimensions and pad layout for CD4097BH.

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of -3 mils to +16 mils applicable to the nominal dimensions shown.